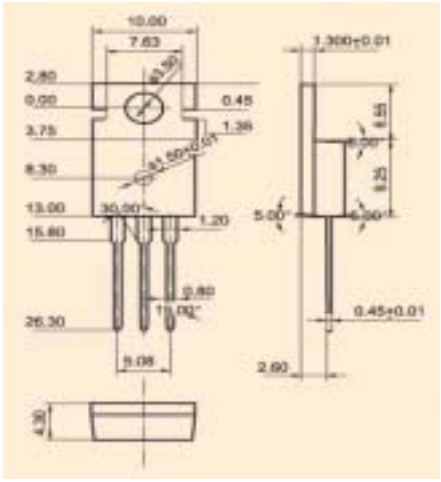
2SA1012

Silicon PNP Transistors

B C E

◆ Features

. With TO-220 package
. Complementary to 2SC2562



TO-220

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V_{CBO}	Collector to base voltage	-60	V
V_{CEO}	Collector to emitter voltage	-50	V
V_{EBO}	Emitter to base voltage	-5	V
I_B	Base current		A
I_C	Collector current	-5	A
P_C	Collector power dissipation	25	W
T_j	Junction temperature	150	℃
T_{stg}	Storage temperature	-55~150	℃

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	Typ	MAX	UNIT
I_{CBO}	Collector-base cut-off current	V_{CB}=-50V; I_E=0			-1	uA
I_{EBO}	Emitter-base cut-off current	V_{EB}=-5V; I_C=0			-1	uA
I_{CEO}	Collector-emitter cut-off current					
V_{CBO}	Collector-base breakdown voltage					
$V_{(BR)ceo}$	Collector-emitter breakdown voltage	I_C=-10mA;I_B=0	-50			V
V_{EBO}	Emitter-base breakdown voltage					
$V_{CE(sat-1)}$	Collector-emitter saturation voltages	I_C=-8A; I_B=-0.15A		-0.2	-0.4	V
$V_{CE(sat-2)}$	Collector-emitter saturation voltages					
h_{FE-1}	Forward current transfer ratio	I_C=-1A; V_{CE}=-1V	70		240	
h_{FE-2}	Forward current transfer ratio	I_C=-3A; V_{CE}=-1V	30			
$V_{BE(sat)1}$	Base-emitter saturation voltages	I_C=-8A; I_B=-0.15A		-0.9	-1.2	V
$V_{BE(sat)2}$	Base-emitter saturation voltages					
C_{OB}	Collector Output Capacitance	V_{CB}=-10V; I_E=0;f=1MHz		70		pF
f_T	Transition frepuency	I_C=-1A; V_{CE}=-4V		60		MHz